

Remarks

The present amendment is proffered in response to the pending Office Action of February 27, 2002, in which claims 5, 6, 11-19, and 21 stand rejected and claims 7, 8, 10, and 20 stand objected to.

By this Amendment, objected-to Claims 7 and 20 have been rewritten to incorporate the limitations of their respective base claims, and the base claims 5 and 11 have been cancelled. The other pending claims have been amended to redirect their dependencies respectively. Applicants respectfully submit that their claim set recites patentable subject matter over the prior art.

Accordingly, Applicants respectfully request entry of the present Amendment and passage of their subject application to issuance in view thereof. Should the Examiner have any comments, questions, or suggestions, please do not hesitate to contact the undersigned attorney at the telephone number and/or email address set forth below.

Respectfully submitted,
For: Furukawa et al.

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Exhibit A**VERSION WITH MARKINGS TO SHOW CHANGES MADE****In the claims:**

Cancel Claims 5 and 11, without prejudice.

6. (Amended) The FET of claim 7 [5], wherein said second implant comprises an extension implant.

7. (Twice Amended) An [The] FET [as recited in claim 7], [further] comprising:
a gate having a top and bottom portion, the top portion having a width that is greater than the width of the bottom portion;
a first diffusion self-aligned to the bottom portion;
a second implant defined by said top portion; and a spacer adjacent said top portion and a third implant defined by said spacer.

10. (Twice Amended) The FET of claim 20 [11], wherein said first conductive material is on a gate dielectric and said gate dielectric is on a substrate.

12. (Twice Amended) The FET of claim 20 [11], wherein said first material comprises a first semiconductor material.

15. (Twice Amended) The FET of claim 20 [11], wherein said second conductive material comprises polysilicon.

16. (Twice Amended) The FET of claim 20 [11], wherein said first conductive material comprises polysilicon.

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19. (Twice Amended) The FET of claim 20 [11], wherein said second conductive material comprises a silicide.
20. (Amended) An [The] FET [of claim 9], [further] comprising a gate, said gate comprising first conductive material and a second conductive material different from said first conductive material, said second conductive material on said first conductive material, wherein said second conductive material extends beyond said first conductive material to provide a T-shaped gate, wherein said first material has a dimension less than a photolithographic minimum dimension, and a spacer along sidewalls of said second conductive material.

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